

Triacs

sensitive gate

BT136 series E

GENERAL DESCRIPTION

Passivated, sensitive gate triacs in a plastic envelope, intended for use in general purpose bidirectional switching and phase control applications, where high sensitivity is required in all four quadrants.

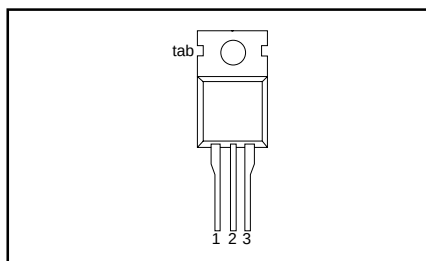
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	UNIT
V_{DRM}	BT136- Repetitive peak off-state voltages	600E 600	800E 800	V
$I_{\text{T(RMS)}}$	RMS on-state current	4	4	A
I_{TSM}	Non-repetitive peak on-state current	25	25	A

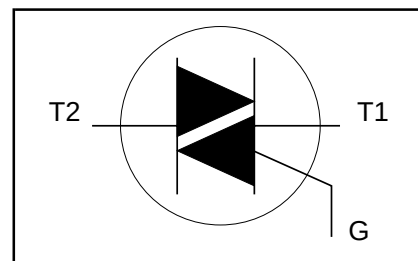
PINNING - TO220AB

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
tab	main terminal 2

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
				-600 600 ¹	-800 800	
V_{DRM}	Repetitive peak off-state voltages		-			V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{mb}} \leq 107^\circ\text{C}$	-	4		A
I_{TSM}	Non-repetitive peak on-state current	full sine wave; $T_{\text{j}} = 25^\circ\text{C}$ prior to surge	-			A
		$t = 20\text{ ms}$	-	25		A
		$t = 16.7\text{ ms}$	-	27		A
		$t = 10\text{ ms}$	-	3.1		A ² s
I^2t	I^2t for fusing		-			
di_{T}/dt	Repetitive rate of rise of on-state current after triggering	$I_{\text{TM}} = 6\text{ A}$; $I_{\text{G}} = 0.2\text{ A}$; $di_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$	-			
		T2+ G+	-	50		A/ μs
		T2+ G-	-	50		A/ μs
		T2- G-	-	50		A/ μs
		T2- G+	-	10		A/ μs
I_{GM}	Peak gate current		-	2		A
V_{GM}	Peak gate voltage		-	5		V
P_{GM}	Peak gate power		-	5		W
$P_{\text{G(AV)}}$	Average gate power		-	0.5		W
T_{stg}	Storage temperature		-40	150		$^\circ\text{C}$
T_{j}	Operating junction temperature	over any 20 ms period	-	125		$^\circ\text{C}$

1 Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 3 A/ μs .

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Thermal resistance junction to mounting base	full cycle	-	-	3.0	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	half cycle in free air	-	-	3.7	K/W
			-	60	-	K/W

STATIC CHARACTERISTICS

 $T_j = 25\ ^\circ\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{GT}	Gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$	-	-	-	-
		T2+ G+	-	2.5	10	mA
		T2+ G-	-	4.0	10	mA
		T2- G-	-	5.0	10	mA
		T2- G+	-	11	25	mA
I_L	Latching current	$V_D = 12\text{ V}$; $I_{GT} = 0.1\text{ A}$	-	-	-	-
		T2+ G+	-	3.0	15	mA
		T2+ G-	-	10	20	mA
		T2- G-	-	2.5	15	mA
		T2- G+	-	4.0	20	mA
I_H	Holding current	$V_D = 12\text{ V}$; $I_{GT} = 0.1\text{ A}$	-	2.2	15	mA
V_T	On-state voltage	$I_T = 5\text{ A}$	-	1.4	1.70	V
V_{GT}	Gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$	-	0.7	1.5	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\ ^\circ\text{C}$	0.25	0.4	-	V
I_D	Off-state leakage current	$V_D = V_{DRM(max)}$; $T_j = 125\ ^\circ\text{C}$	-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

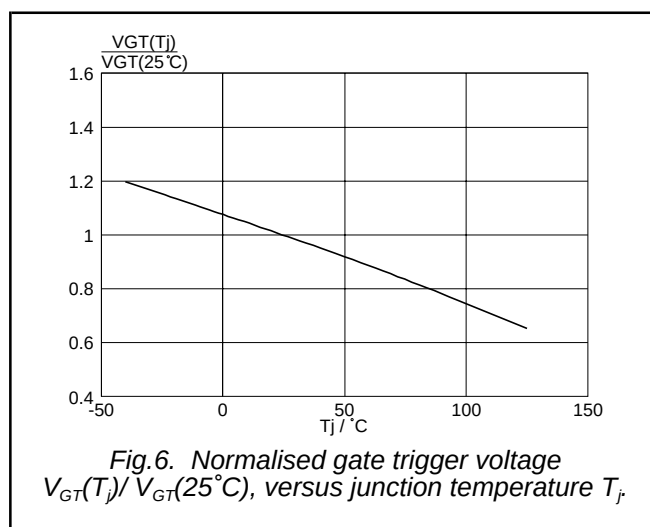
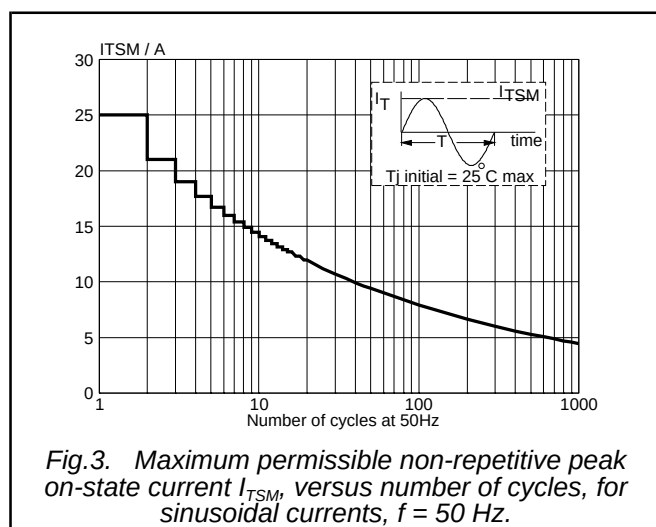
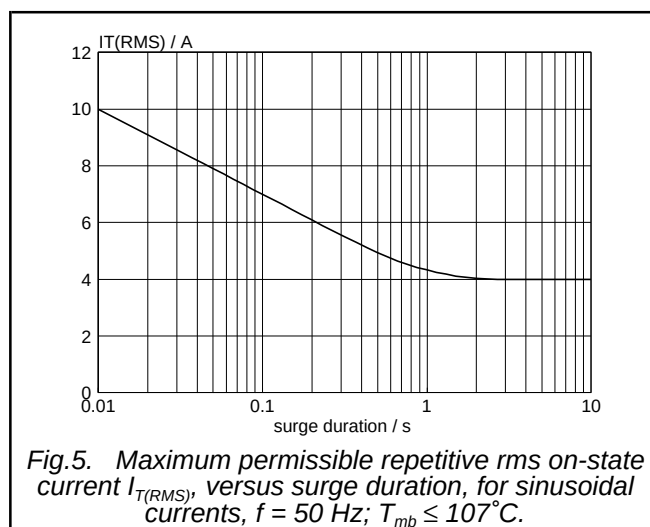
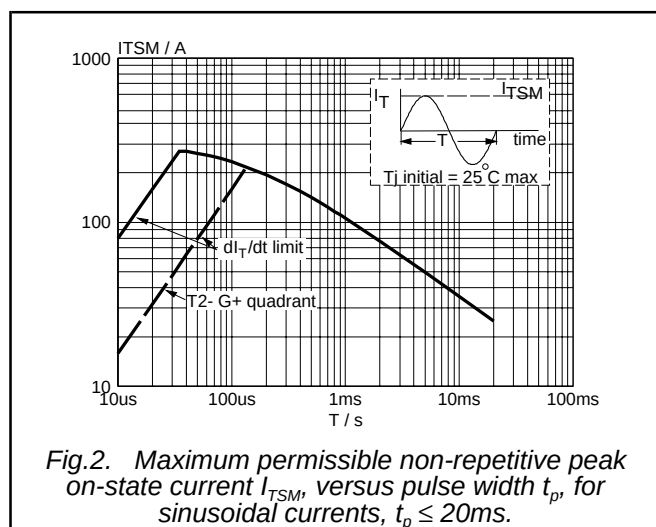
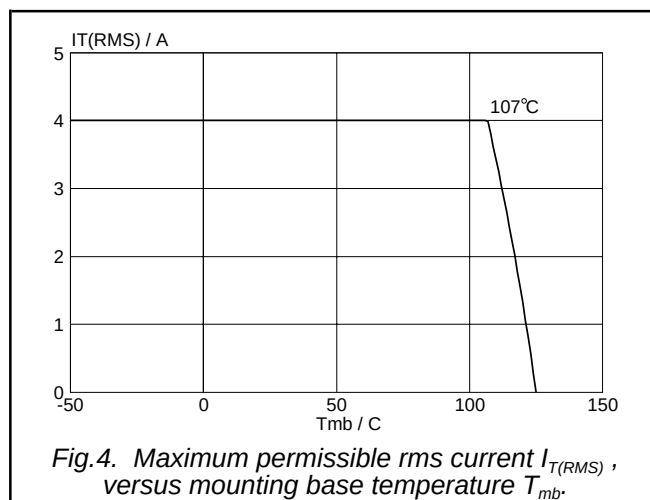
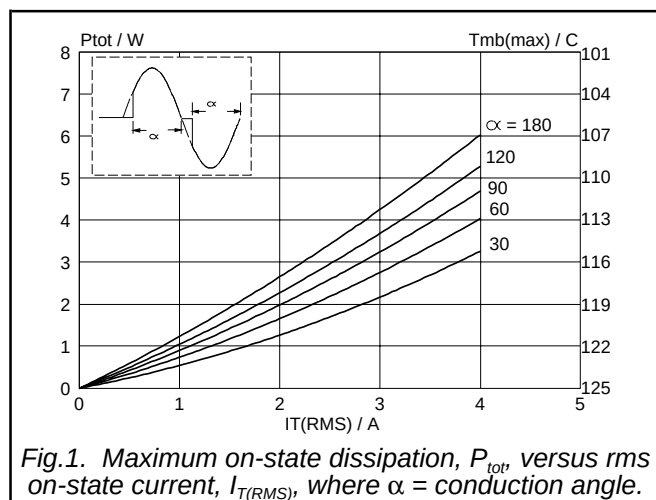
 $T_j = 25\ ^\circ\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV_D/dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)}$; $T_j = 125\ ^\circ\text{C}$; exponential waveform; gate open circuit	-	50	-	V/ μs
t_{gt}	Gate controlled turn-on time	$I_{TM} = 6\text{ A}$; $V_D = V_{DRM(max)}$; $I_G = 0.1\text{ A}$; $di_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	μs

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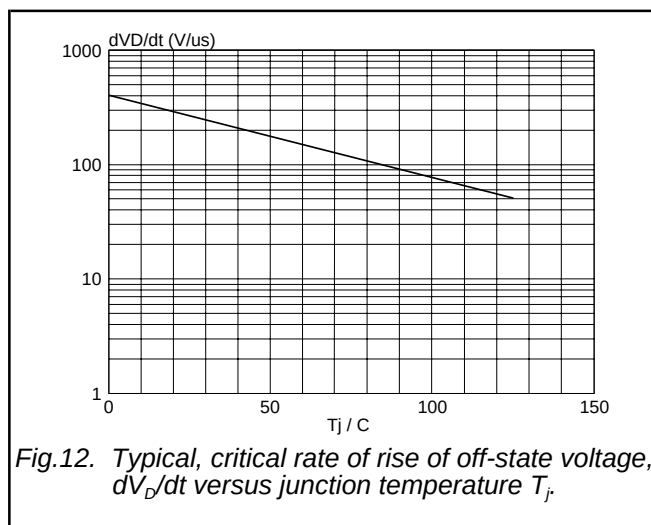
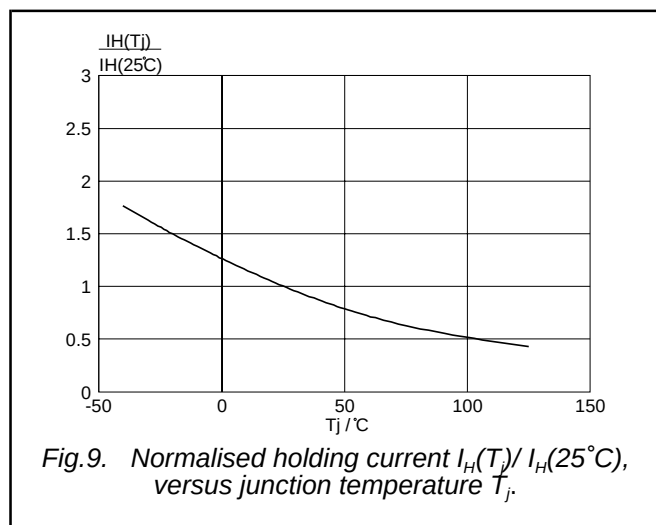
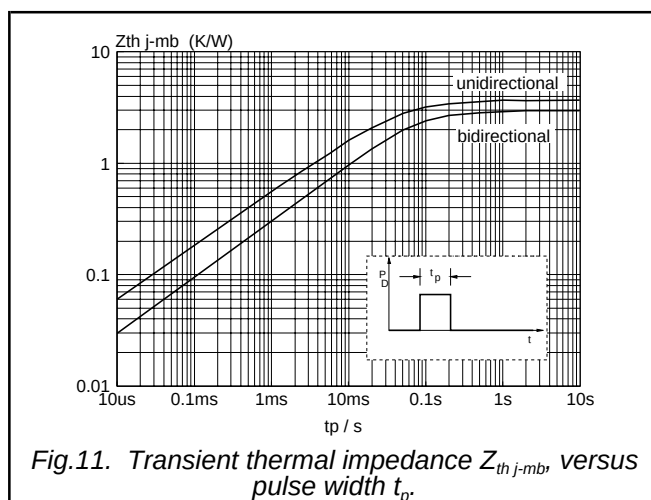
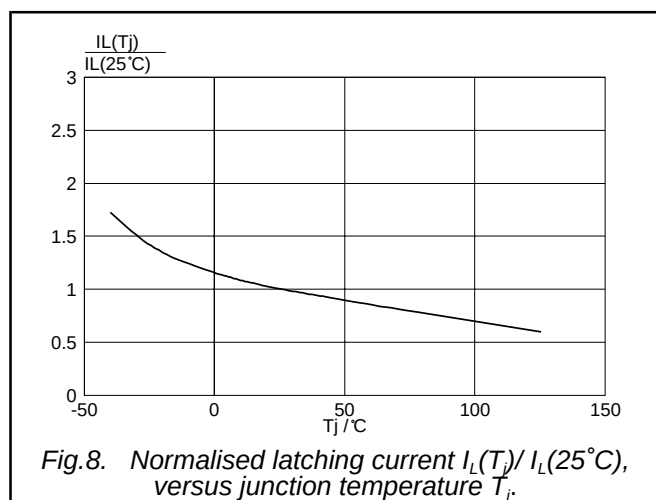
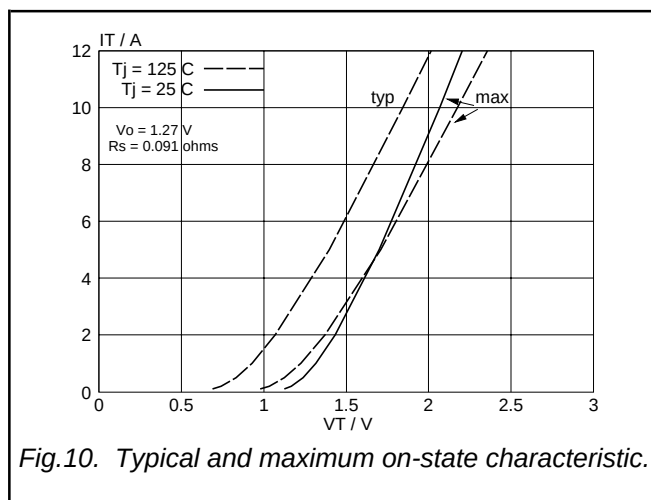
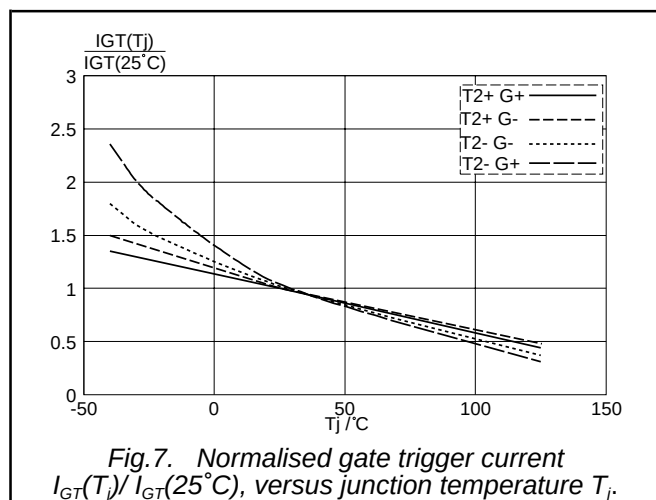
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MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

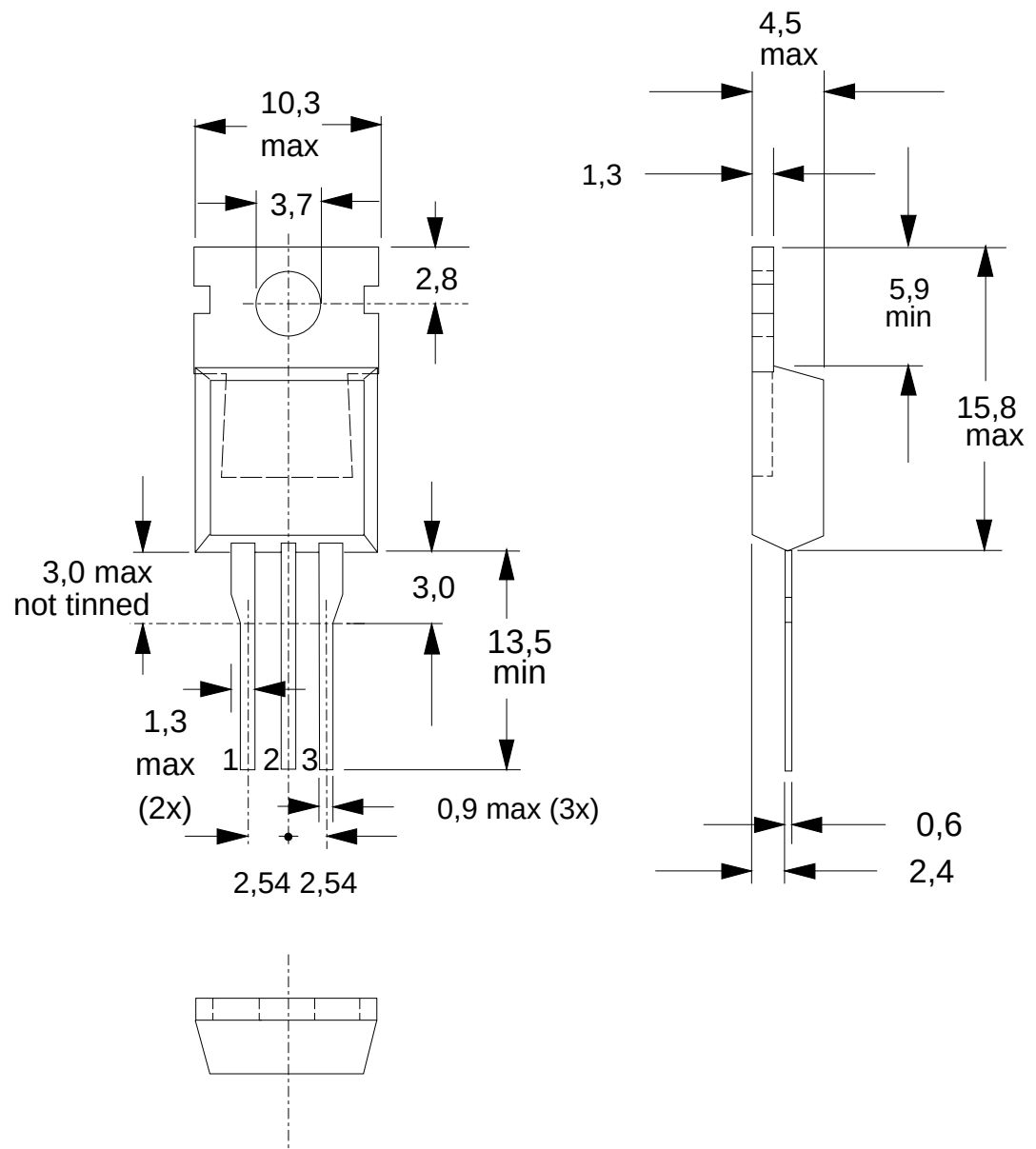


Fig.13. SOT78 (TO220AB). pin 2 connected to mounting base.

Notes

1. Refer to mounting instructions for SOT78 (TO220) envelopes.
2. Epoxy meets UL94 V0 at 1/8".